

isc N-Channel MOSFET Transistor

18N60

• FEATURES

- · With TO-247 packaging
- · High speed switching
- Standard level gate drive
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Power supply
- Switching applications

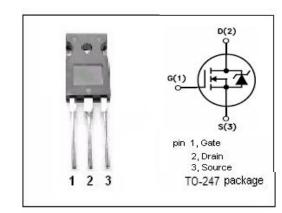


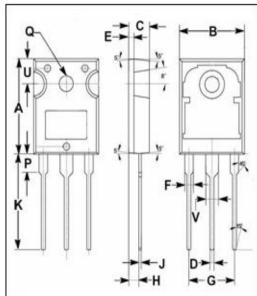
• ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--------------------------------|---------|---------------|
| V _{DSS} | Drain-Source Voltage | 600 | V |
| V _{GSS} | Gate-Source Voltage | ±30 | V |
| I _D | Drain Current-Continuous | 18 | А |
| I _{DM} | Drain Current-Single Pulsed | 48 | А |
| P _D | Total Dissipation | 360 | W |
| Tj | Operating Junction Temperature | -55~150 | ${\mathbb C}$ |
| T _{stg} | Storage Temperature | -55~150 | ${\mathbb C}$ |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|-----------|------------------------------------|------|--------------|
| Rth(ch-c) | Channel-to-case thermal resistance | 0.35 | °C /W |





| | mm | | |
|-----|-------|-------|--|
| DIM | MIN | MAX | |
| Α | 19.80 | 20.20 | |
| В | 15.40 | 15.80 | |
| C | 4.90 | 5.10 | |
| D | 0.90 | 1.10 | |
| E | 1.40 | 1.60 | |
| F | 1.90 | 2.10 | |
| G | 10.80 | 11.00 | |
| Н | 2.40 | 2.60 | |
| J | 0.50 | 0.70 | |
| K | 19.50 | 20.50 | |
| P | 3.90 | 4.10 | |
| Q | 3.30 | 3.50 | |
| U | 5.20 | 5.40 | |
| V | 2.90 | 3.10 | |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|---------------------|--------------------------------|---|-----|-----|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 0.25mA | 600 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =±30V; I _D =0.25mA | 2.0 | | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =9A | | | 0.4 | Ω |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±30V;V _{DS} = 0V | | | ±0.1 | μА |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 600V; V _{GS} = 0V | | | 25 | μА |
| V _{SDF} | Diode forward voltage | I _{SD} =18A, V _{GS} = 0 V | | | 1.5 | V |



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